Complementary Silicon Power Transistors

These complementary silicon power transistors are designed for high-speed switching applications, such as switching regulators and high frequency inverters. The devices are also well-suited for drivers for high power switching circuits.

Features

- Fast Switching $t_f = 90 \text{ ns (Max)}$
- Key Parameters Specified @ 100°C
- Complementary Pairs Simplify Circuit Designs
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Emitter Voltage	V_{CEV}	100	Vdc
Emitter Base Voltage	V_{EB}	7.0	Vdc
Collector Current -Continuous -Peak (Note 1)	I _C I _{CM}	15 20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	83 0.67	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T _L	275	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Width \leq 6.0 ms, Duty Cycle \leq 50%.

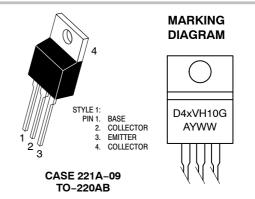
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ON Semiconductor®

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15 A COMPLEMENTARY SILICON POWER TRANSISTORS 80 V, 83 W



x = 4 or 5

A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
D44VH10	TO-220	50 Units/Rail
D44VH10G	TO-220 (Pb-Free)	50 Units/Rail
D45VH10	TO-220	50 Units/Rail
D45VH10G	TO-220 (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTI	cs						
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 25 \text{ mAdc}, I_B = 0)$		V _{CEO(sus)}	80	_	-	Vdc	
Collector–Emitter Cutoff Current $(V_{CE} = Rated\ V_{CEV},\ V_{BE(off)} = 4.0\ Vdc) \\ (V_{CE} = Rated\ V_{CEV},\ V_{BE(off)} = 4.0\ Vdc,\ T_{C} = 100^{\circ}C)$		I _{CEV}	- -	- -	10 100	μAdc	
Emitter Base Cutoff Current $(V_{EB} = 7.0 \text{ Vdc}, I_C = 0)$			I _{EBO}	-	-	10	μAdc
ON CHARACTERISTIC	S (Note 2)						
DC Current Gain $(I_C = 2.0 \text{ Adc}, V_{CE} = (I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Adc})$	· · · · · · · · · · · · · · · · · · ·		h _{FE}	35 20			-
Collector–Emitter Sati (I_C = 8.0 Adc, I_B = 0 (I_C = 8.0 Adc, I_B = 0 (I_C = 15 Adc, I_B = 3	0.4 Adc) 0.8 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	V _{CE(sat)}	- - -	- - -	0.4 1.0 0.8 1.5	Vdc
	0.4 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	V _{BE(sat)}	- - - -	- - - -	1.2 1.0 1.1 1.5	Vdc
DYNAMIC CHARACTE	RISTICS			•	•		
Current Gain Bandwidth Product (I _C = 0.1 Adc, V _{CE} = 10 Vdc, f = 20 MHz)		f _T	-	50	-	MHz	
Output Capacitance $ (V_{CB} = 10 \text{ Vdc}, I_{C} = 0, f_{test} = 1.0 \text{ MHz}) $ D44VH10 D45VH10		C _{ob}	- -	120 275	-	pF	
SWITCHING CHARAC	TERISTICS		T	T	_		
Delay Time			t _d	-	-	50	ns
Rise Time	(V _{CC} = 20 Vdc, I _C = 8.0 Adc,		t _r	_	_	250	
Storage Time	I _{B1} = I _{B2} = 0.8 Adc)		ts	-	-	700	
Fall Time			t _f	-	-	90	

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

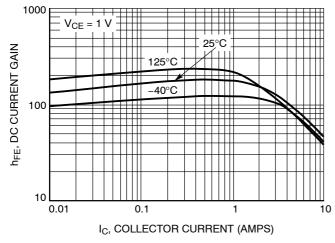


Figure 1. D44VH10 DC Current Gain

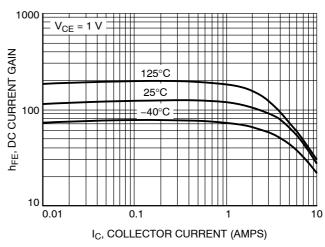


Figure 2. D45VH10 DC Current Gain

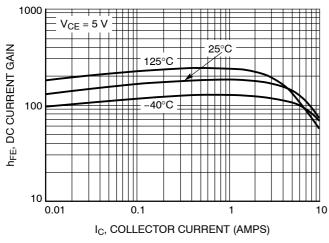


Figure 3. D44VH10 DC Current Gain

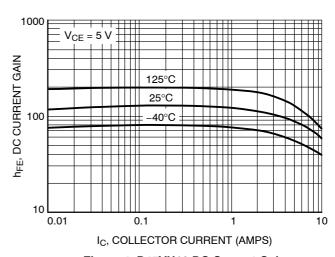


Figure 4. D45VH10 DC Current Gain

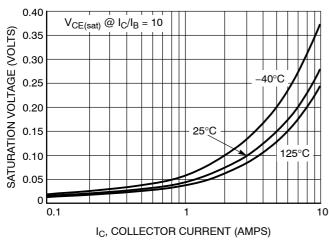


Figure 5. D44VH10 ON-Voltage

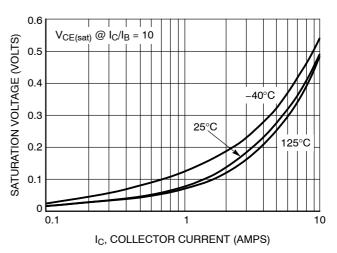


Figure 6. D45VH10 ON-Voltage

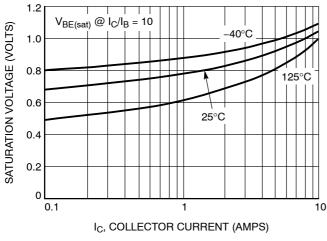


Figure 7. D44VH10 ON-Voltage

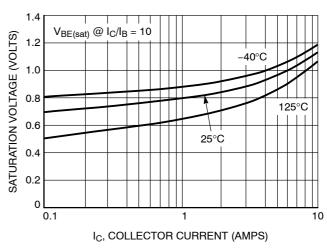


Figure 8. D45VH10 ON-Voltage

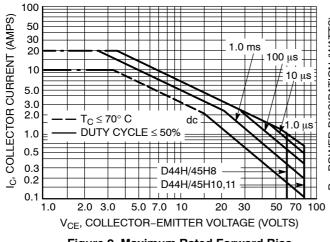


Figure 9. Maximum Rated Forward Bias Safe Operating Area

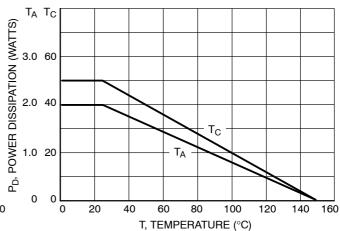


Figure 10. Power Derating

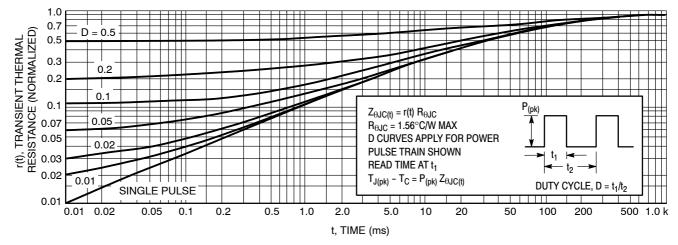
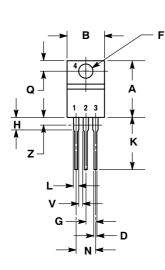
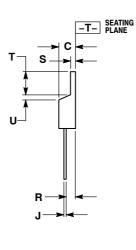


Figure 11. Thermal Response

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AG**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES MILLIMETER		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

PIN 1. BASE

- COLLECTOR
- EMITTER
- COLLECTOR

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